

Description

The 74LVC1G10 is a single 3-input positive NAND gate with a standard push-pull output. The device is designed for operation with a power supply range of 1.65V to 5.5V. The inputs are tolerant to 5.5V allowing this device to be used in a mixed voltage environment. The device is fully specified for partial power down applications using IOFF. The IOFF circuitry disables the output preventing damaging current backflow when the device is powered down.

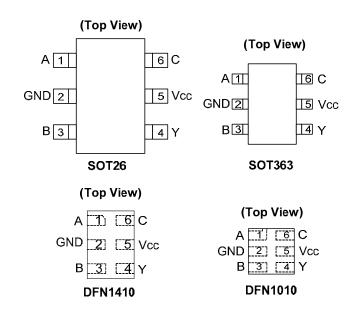
The gate performs the positive Boolean function:

$$Y = \overline{A \bullet B \bullet C}$$
 or $Y = \overline{A} + \overline{B} + \overline{C}$

Features

- Wide Supply Voltage Range from 1.65V to 5.5V
- ± 24mA Output Drive at 3.3V
- CMOS low power consumption
- IOFF Supports Partial-Power-Down Mode Operation
- Inputs accept up to 5.5V
- ESD Protection Exceeds JESD 22 200-V Machine Model (A115-A) 2000-V Human Body Model (A114-A)
- Latch-Up Exceeds 100mA per JESD 78, Class II
- Range of Package Options
- SOT26, SOT363, DFN1410, and DFN1010: Available in "Green" Molding Compound (no Br, Sb)
- Lead Free Finish/ RoHS Compliant (Note 1)

Pin Assignments



Applications

- Voltage Level Shifting
- General Purpose Logic
- · Power Down Signal Isolation
- Wide array of products such as:
 - o PCs, networking, notebooks, netbooks, PDAs
 - o Computer peripherals, hard drives, CD/DVD ROM
 - o TV, DVD, DVR, set top box
 - o Cell Phones, Personal Navigation / GPS
 - o MP3 players ,Cameras, Video Recorders

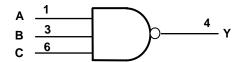
Notes: 1. EU Directive 2002/95/EC (RoHS). All applicable RoHS exemptions applied. Please visit our website at http://www.diodes.com/products/lead_free.html.



Pin Descriptions

Pin Name	Description
Α	Data Input
GND	Ground
В	Data Input
Y	Data Output
V _{CC}	Supply Voltage
С	Data Input

Logic Diagram



Function Table

	Inputs						
Α	В	С	Υ				
Н	Н	Н	L				
L	X	Χ	Н				
Х	L	Χ	Н				
Х	Х	L	Н				

Absolute Maximum Ratings (Note 2)

Symbol	Description	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	KV
ESD MM	Machine Model ESD Protection	200	V
V _{CC}	Supply Voltage Range	-0.5 to 6.5	V
VI	Input Voltage Range	-0.5 to 6.5	V
Vo	Voltage applied to output in high impedance or I _{OFF} state	-0.5 to 6.5	V
Vo	Voltage applied to output in high or low state	-0.3 to V _{CC} +0.5	V
I _{IK}	Input Clamp Current V _I <0	-50	mA
I _{OK}	Output Clamp Current	-50	mA
Io	Continuous output current	±50	mA
	Continuous current through Vdd or GND	±100	mA
T_J	Operating Junction Temperature	-40 to 150	°C
T _{STG}	Storage Temperature	-65 to 150	°C

Notes: 2. Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.



Recommended Operating Conditions (Note 3)

Symbol		Parameter	Min	Max	Unit
\/	Operating Voltage	Operating	1.65	5.5	V
V _{CC}	Operating Voltage	Data retention only	1.5		V
		$V_{CC} = 1.65V \text{ to } 1.95V$	0.65 X V _{CC}		
V	High lovel Input Voltage	$V_{CC} = 2.3V \text{ to } 2.7V$	1.7		\/
V _{IH}	High-level Input Voltage	$V_{CC} = 3V$ to 3.6V	2		V
		$V_{CC} = 4.5V \text{ to } 5.5V$	0.7 X V _{CC}		
		V _{CC} = 1.65V to 1.95V		0.35 X V _{CC}	
	Law law line of calle	V _{CC} = 2.3V to 2.7V		0.7	
V_{IL}	Low-level input voltage	V _{CC} = 3V to 3.6V		0.8	V
		V _{CC} = 4.5V to 5.5V		0.3 X V _{CC}	
VI	Input Voltage		0	5.5	V
Vo	Output Voltage		0	V _{CC}	V
		V _{CC} = 1.65V		-4	
		V _{CC} = 2.3V		-8	
I _{OH}	High-level output current	V 2V		-16	mA
		$V_{CC} = 3V$		-24	
		V _{CC} = 4.5V		-32	
		V _{CC} = 1.65V		4	
		V _{CC} = 2.3V		8	
I_{OL}	Low-level output current	V 2V		16	mA
		$V_{CC} = 3V$		24	
		$V_{CC} = 4.5V$		32	
	Innut transition via a f-11	$V_{CC} = 1.8V \pm 0.15V, 2.5V \pm 0.2V$		20	
Δt/ΔV	Input transition rise or fall rate	$V_{CC} = 3.3V \pm 0.3V$		10	ns/V
	late	$V_{CC} = 5V \pm 0.5V$		5	
T _A	Operating free-air temperature		-40	125	°C

Notes: 3. Unused inputs should be held at Vcc or Ground.



Electrical Characteristics $T_A = -40$ °C to 85°C (All typical values are at $V_{CC} = 3.3V$, $T_A = 25$ °C)

Symbol	Parameter	Test Conditions	V _{CC}	Min	Тур.	Max	Unit
		$I_{OH} = -100 \mu A$	1.65V to 5.5V	V _{CC} – 0.1			
		$I_{OH} = -4mA$	1.65V	1.2			
V	High Level Output	$I_{OH} = -8mA$	2.3V	1.9			V
V _{OH}	Voltage	I _{OH} = -16mA	3V	2.4			V
		I _{OH} = -24mA	3 V	2.3			
		$I_{OH} = -32mA$	4.5V	3.8			
		$I_{OL} = 100 \mu A$	1.65V to 5.5V			0.1	
		$I_{OL} = 4mA$	1.65V			0.45	
\/ - ·	High-level Input Voltage	$I_{OL} = 8mA$	2.3V			0.3	V
V_{OL}	Tilgri-level lilput voltage	$I_{OL} = 16mA$	3V			0.4	V
		$I_{OL} = 24mA$	30			0.55	
		$I_{OL} = 32mA$	4.5V			0.55	
lı	Input Current	$V_I = 5.5 \text{ V or GND}$	0 to 5.5V			± 5	μΑ
I _{OFF}	Power Down Leakage Current	V_I or $V_O = 5.5V$	0			± 10	μΑ
Icc	Supply Current	$V_I = 5.5V$ of GND $I_{O}=0$	1.65V to 5.5V			10	μΑ
ΔI _{CC}	Additional Supply Current	Input at V _{CC} –0.6V	3V to 5.5V			500	μA



Electrical Characteristics $T_A = -40$ °C to 125°C (All typical values are at $V_{CC} = 3.3$ V, $T_A = 25$ °C)

Symbol	Parameter	Test Conditions	V _{CC}	Min	Тур.	Max	Unit	
		I _{OH} = -100μA	1.65V to 5.5V	V _{CC} - 0.1				
		$I_{OH} = -4mA$	1.65V	0.95				
V	High Level Output	$I_{OH} = -8mA$	2.3V	1.7			V	
V_{OH}	Voltage	I _{OH} = -16mA	2)/	1.9]	
		I _{OH} = -24mA	3V	2.0				
		I _{OH} = -32mA	4.5V	3.4				
		I _{OL} = 100μA	1.65V to 5.5V			0.1		
		I _{OL} = 4mA	1.65V			0.70	1	
\/	High level legat Valtage	$I_{OL} = 8mA$	2.3V			0.45] ,,	
V_{OL}	High-level Input Voltage	I _{OL} = 16mA	2)/			0.60	V	
		I _{OL} = 24mA	3V			0.80	1	
		I _{OL} = 32mA	4.5V			0.80	1	
I _I	Input Current	V _I = 5.5 V or GND	0 to 5.5V			± 20	μΑ	
I _{OFF}	Power Down Leakage Current	V_I or $V_O = 5.5V$	0			± 20	μΑ	
I _{CC}	Supply Current	$V_I = 5.5V$ of GND $I_O=0$	1.65V to 5.5V			40	μA	
ΔI _{CC}	Additional Supply Current	Input at V _{CC} -0.6V	3V to 5.5V			5000	μA	
Ci	Input Capacitance	$V_i = V_{CC} - \text{or GND}$	3.3		4		pF	
		SOT26			204			
θ_{JA}	Thermal Resistance	SOT363	(Note 4)		371		°C/W	
ОЈД	Junction-to-Ambient	DFN1410	(Note 4)		430			
		DFN1010			510			
		SOT26			52			
$\theta_{ m JC}$	Thermal Resistance	SOT363	(Note 4)		143		°C/W	
OJC	Junction-to-Case	DFN1410	(14016 4)		190		J, vv	
		DFN1010			250			

Package Characteristics (All typical values are at Vcc = 3.3V, T_A = 25°C)

Symbol	Parameter	Test Conditions	V _{CC}	Min	Тур.	Max	Unit
CI	Input Capacitance	$V_I = V_{CC} - \text{or GND}$	3.3		3.5		pF
		SOT26			204		
	Thermal Resistance	SOT363	(1)		371		00.004
θ_{JA}	Junction-to-Ambient	DFN1410	(Note 4)		430		°C/W
		DFN1010			510		
		SOT26			52		
	Thermal Resistance SOT363	(1)		143		00.004	
θ_{JC}	Junction-to-Case	DFN1410	(Note 4)		190		°C/W
		DFN1010			250		

Notes: 4. Test condition for SOT26, SOT363, DFN1410 and DFN1010 : Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.



Switching Characteristics

 $T_A = -40$ °C to 85°C, CL = 15pF (see Figure 1)

Parameter	From	TO (OUTPUT)	V _{CC} = ± 0.		V _{CC} = ± 0	2.5V 0.2V	V _{CC} = ± 0	3.3V .3V		= 5V 0.5V	Unit
	(Input)	(001701)	Min	Max	Min	Max	Min	Max	Min	Max	
t _{pd}	Any	Y	1.0	14.8	0.7	5.5	0.7	3.8	0.7	2.7	ns

 $T_A = -40$ °C to 85°C, CL = 30 or 50pF (see Figure 2)

Parameter	From (Input)	TO (OUTPUT)	V _{CC} = ± 0.	1.8V 15V	V _{CC} = ± 0	2.5V .2V	V _{CC} = ± 0	: 3.3V :3V		; = 5V 0.5V	Unit
	(iliput)	(001701)	Min	Max	Min	Max	Min	Max	Min	Max	
t _{pd}	Any	Y	1.0	18.0	0.7	6.5	0.7	5	0.7	3.6	ns

 $T_A = -40$ °C to 125°C, CL = 15 pF (see Figure 1)

Parameter	From (Input)	TO (OUTPUT)	V _{CC} = ± 0.		V _{CC} =	: 2.5V).2V	V _{CC} = ± 0			= 5V 0.5V	Unit
	(ilipat)	(331131)	Min	Max	Min	Max	Min	Max	Min	Max	
t _{pd}	Any	Y	1.0	17.7	0.7	6.6	0.7	4.6	0.7	3.3	ns

 $T_A = -40$ °C to 125°C, CL = 30 or 50pF (see Figure 2)

Parameter	From (Input)	TO (OUTPUT)	V _{CC} = ± 0.		V _{CC} = ± 0	: 2.5V :2V	V _{CC} = ± 0	3.3V .3V		= 5V 0.5V	Unit
	(ilipat)	(001101)	Min	Max	Min	Max	Min	Max	Min	Max	
t _{pd}	Any	Y	1.0	21.6	0.7	7.8	0.7	6.0	0.7	4.3	ns

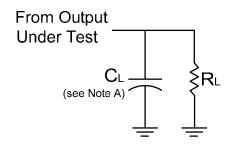
Operating Characteristics

 $T_A = 25$ °C

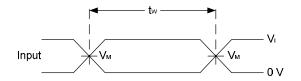
	Parameter	Test Conditions	V _{CC} = 1.8V Typ.	V _{CC} = 2.5V Typ.	V _{CC} = 3.3V Typ.	V _{CC} = 5V Typ.	Unit
C _{pd}	Power dissipation capacitance	f = 10 MHz	17	18	19	22	pF



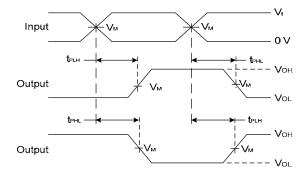
Parameter Measurement Information



V	Inputs		V	C	В
V _{CC}	VI	t _r /t _f	V _M	CL	R _L
1.8V±0.15V	V _{CC}	≤2ns	V _{CC} /2	15pF	1ΜΩ
2.5V±0.2V	V _{CC}	≤2ns	V _{CC} /2	15pF	1ΜΩ
3.3V±0.3V	3V	≤2.5ns	1.5V	15pF	1ΜΩ
5V±0.5V	V_{CC}	≤2.5ns	V _{CC} /2	15pF	1ΜΩ



Voltage Waveform Pulse Duration



Voltage Waveform
Propagation Delay Times
Inverting and Non Inverting Outputs

Figure 1. Load Circuit and Voltage Waveforms

Notes: A. Includes test lead and test apparatus capacitance.

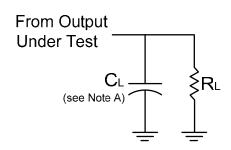
B. All pulses are supplied at pulse repetition rate ≤ 10 MHz

C. Inputs are measured separately one transition per measurement

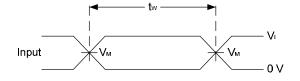
D. t_{PLH} and t_{PHL} are the same as t_{PD}



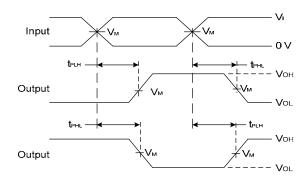
Parameter Measurement Information (cont.)



V _{CC}	Inputs		V	C	В
	VI	t _r /t _f	V _M	CL	R _L
1.8V±0.15V	V _{CC}	≤2ns	V _{CC} /2	30pF	1ΚΩ
2.5V±0.2V	V _{CC}	≤2ns	V _{CC} /2	30pF	500Ω
3.3V±0.3V	3V	≤2.5ns	1.5V	50pF	500Ω
5V±0.5V	V_{CC}	≤2.5ns	V _{CC} /2	50pF	500Ω



Voltage Waveform Pulse Duration



Voltage Waveform
Propagation Delay Times
Inverting and Non Inverting Outputs

Figure 2. Load Circuit and Voltage Waveforms

Notes: A . Includes test lead and test apparatus capacitance.

- B. All pulses are supplied at pulse repetition rate ≤ 10 MHz
- C. Inputs are measured separately one transition per measurement
- D. t_{PLH} and t_{PHL} are the same as t_{PD}



Ordering Information

T4LVC1G 10 XXX - 7

Logic Device Function Package Packing

74: Logic Prefix 10: 3-Input W6: SOT26 7: Tape & Reel

LVC : 1.65 to 5.5V NAND - Gate DW : SOT363
Family FW4 : DFN1010
1G : One gate FZ4 : DFN1410

	Device	Package	Packaging (Note 7)	7" Tape and Reel		
	Device	Code		Quantity	Part Number Suffix	
Pb ,	74LVC1G10W6-7	W6	SOT26	3000/Tape & Reel	-7	
Pb ,	74LVC1G10DW-7	DW	SOT363	3000/Tape & Reel	-7	
Pb,	74LVC1G10FW4-7	FW4	DFN1010	5000/Tape & Reel	-7	
P	74LVC1G10FZ4-7	FZ4	DFN1410	5000/Tape & Reel	-7	

Notes:

- Pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
- 6. The taping orientation is located on our website at http://www.diodes.com/datasheets/ap02007.pdf



Marking Information

(1) SOT26, SOT363

6 5 4

XXYWX

2 3 XX: Identification code

Y: Year 0~9

<u>W</u>: Week: A~Z: 1~26 week;

a~z: 27~52 week; z represents

52 and 53 week

X: A~Z: Internal Code

Part Number	Package	Identification Code
74LVC1G10W6	SOT26	TU
74LVC1G10DW	SOT363	TU

(2) DFN1010, DFN1410

(Top View)

XX XX: Identification Code

 $\overline{\underline{Y}}$: Year : 0~9

W: Week: A~Z: 1~26 week; a~z: 27~52 week; z represents

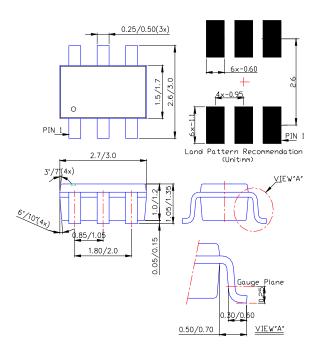
52 and 53 week X: A~Z: Internal code

Part Number	Package	Identification Code
74LVC1G10FW4	DFN1010	TU
74LVC1G10FZ4	DFN1410	TU

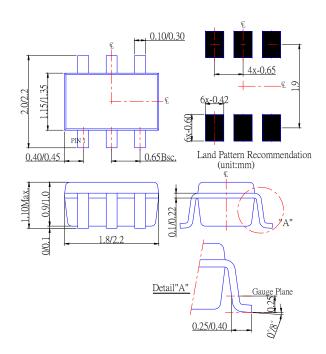


Package Outline Dimensions (All Dimensions in mm)

(1) Package Type: SOT26

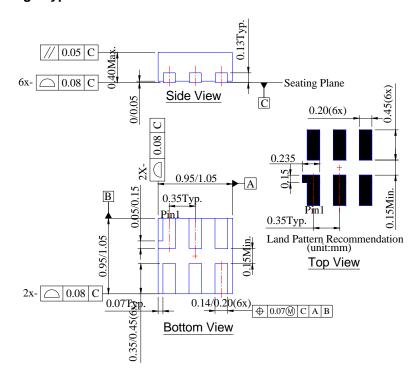


(2) Package Type: SOT363

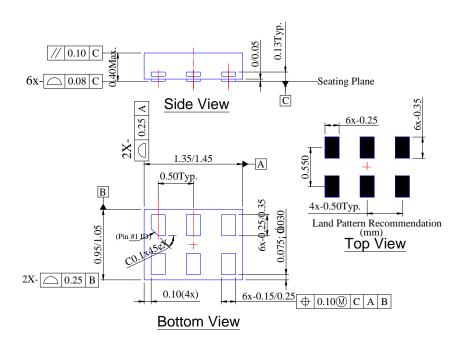




(3) Package Type: DFN1010



(4) Package Type DFN1410





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